



PHOTO DIODE NR6800 Series

ϕ 80 μ m InGaAs AVALANCHE PHOTO DIODE FOR OTDR APPLICATIONS

DESCRIPTION

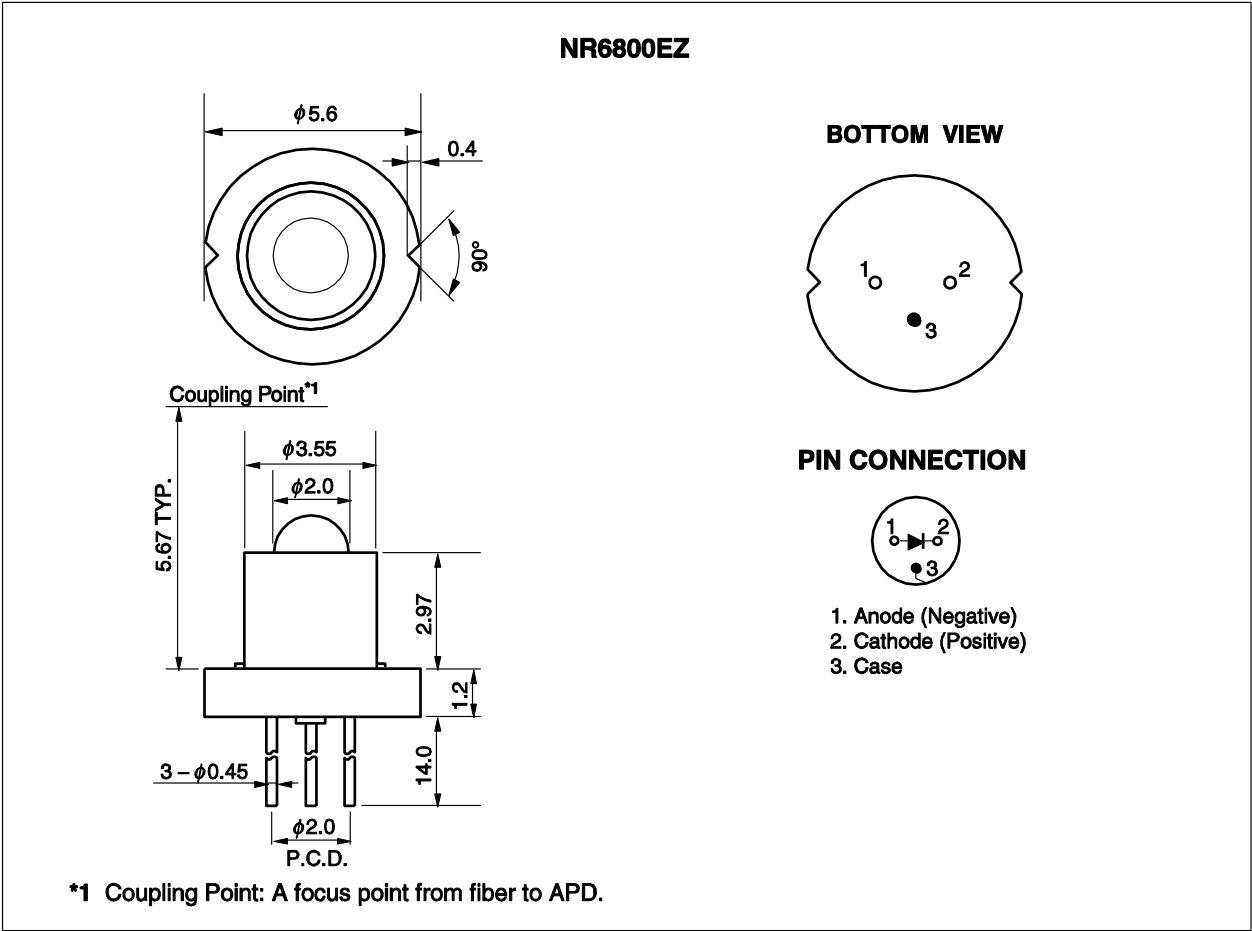
The NR6800 Series is an InGaAs avalanche photo diode, and can be used in OTDR systems.

FEATURES

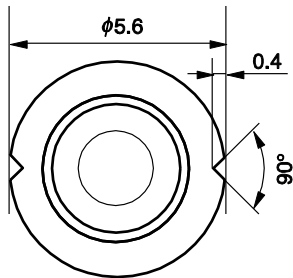
- | | |
|------------------------------|--|
| • Small dark current | $I_D = 5 \text{ nA}$ |
| • Small terminal capacitance | $C_t = 0.50 \text{ pF @ } 0.9 \text{ V}_{(BR)R}$ |
| • High sensitivity | $S = 0.94 \text{ A/W @ } \lambda = 1310 \text{ nm, } M = 1$ |
| • High speed response | $f_c = 1.0 \text{ GHz MIN. @ } \lambda = 1310 \text{ nm, } M = 10$ |
| • Detecting area size | $\phi 80 \mu\text{m}$ |

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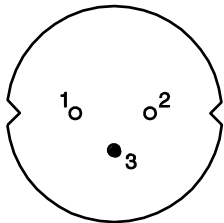
PACKAGE DIMENSION (UNIT: mm)



NR6800SZ



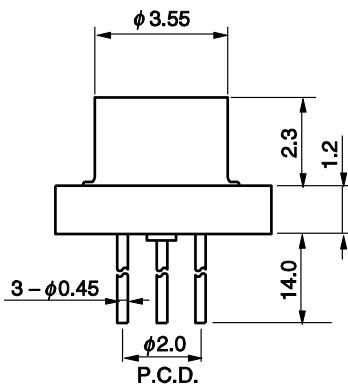
BOTTOM VIEW



PIN CONNECTION



- 1. Anode (Negative)
- 2. Cathode (Positive)
- 3. Case



ORDERING INFORMATION

Part Number	Package
NR6800EZ-AZ	3-pin CAN with ball lens cap
NR6800SZ-AZ	3-pin CAN with flat glass cap

- Remarks**
1. The color of ball lens cap might be observed differently.
 2. The hermetic test will be performed as AQL 1.0%.

ABSOLUTE MAXIMUM RATINGS

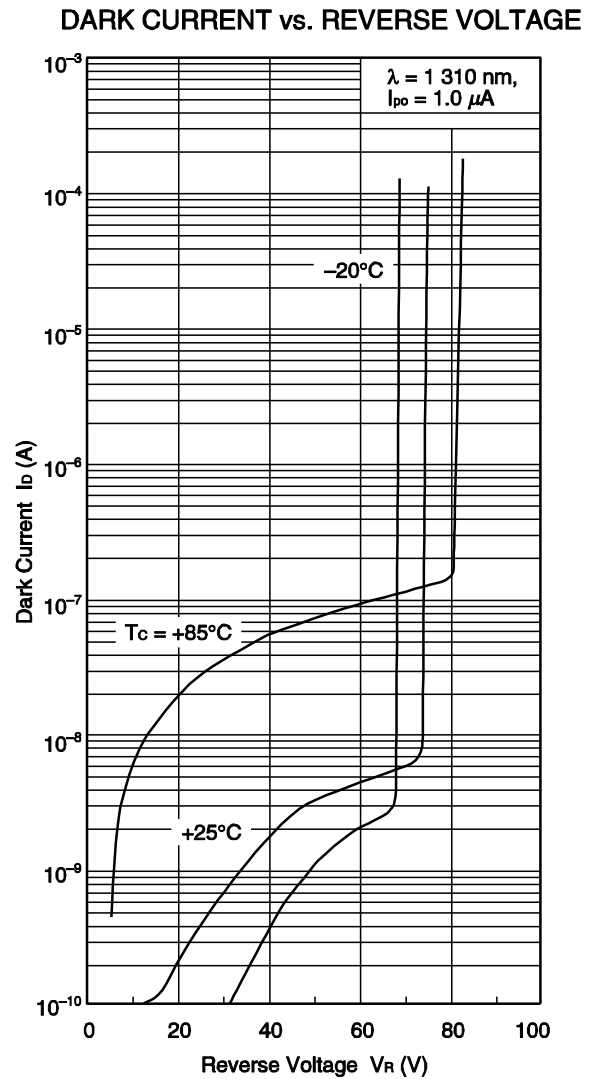
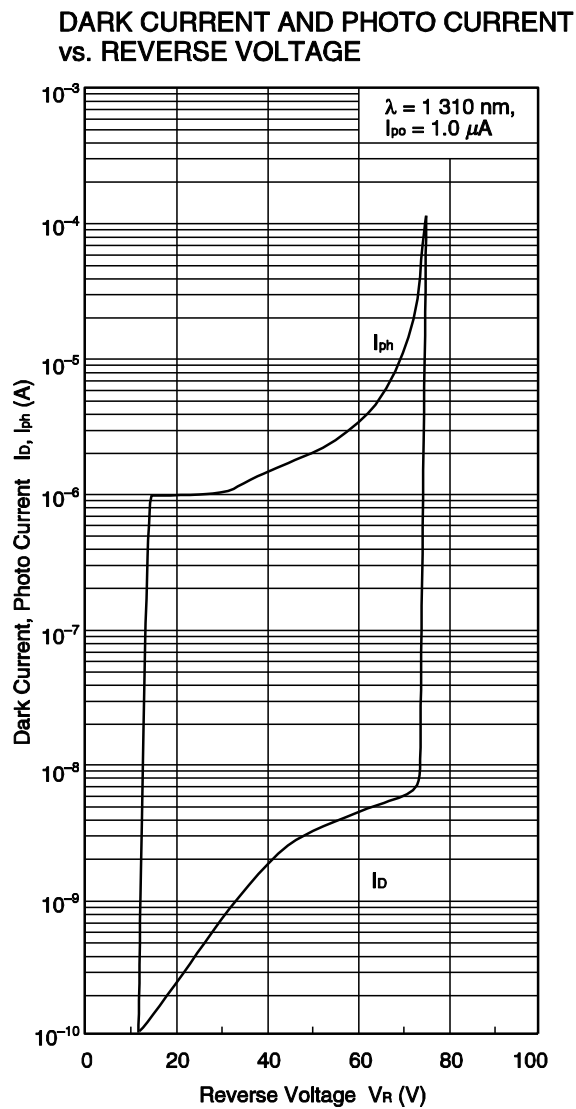
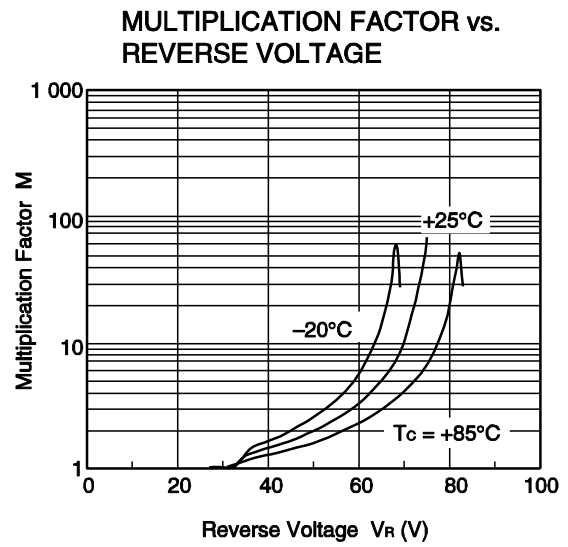
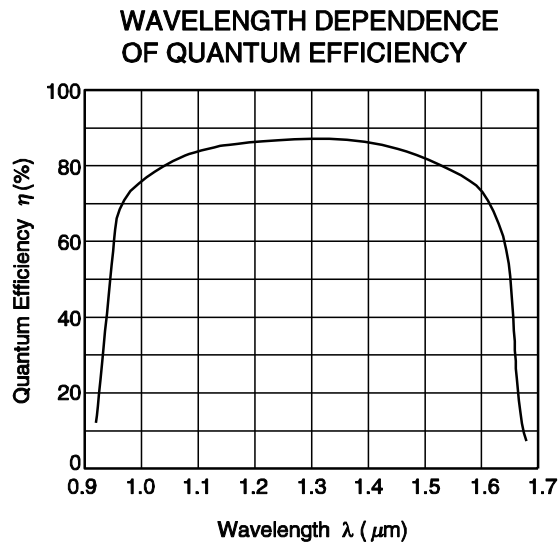
Parameter	Symbol	Ratings	Unit
Forward Current	I_F	10	mA
Reverse Current	I_R	0.5	mA
Operating Case Temperature	T_C	-40 to +85	°C
Storage Temperature	T_{stg}	-40 to +85	°C
Lead Soldering Temperature	T_{sld}	350 (3 sec.)	°C
Relative Humidity (noncondensing)	RH	85	%

ELECTRO-OPTICAL CHARACTERISTICS (T_c = 25°C, unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Reverse Breakdown Voltage	V _{BR}	I _D = 100 μA	50	70	100	V
Temperature Coefficient of Reverse Breakdown Voltage	δ ⁻¹			0.2		%/°C
Dark Current	I _D	V _R = V _{BR} × 0.9		5	30	nA
Terminal Capacitance	C _t	V _R = V _{BR} × 0.9, f = 1 MHz		0.50	0.75	pF
Cut-off Frequency	f _c	λ = 1 310 nm, M = 10	1.0			GHz
Sensitivity	S	λ = 1 310 nm, M = 1	0.80	0.94		A/W
Multiplication Factor	M	λ = 1 310 nm, I _{po} = 1.0 μA, V _R = V (@ I _D = 1 μA)	30	50		

$$*1 \quad \delta = \frac{V_{BR}(25^{\circ}\text{C} + \Delta T^{\circ}\text{C}) - V_{BR}(25^{\circ}\text{C})}{\Delta T^{\circ}\text{C} \cdot V_{BR}(25^{\circ}\text{C})}$$

TYPICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$, unless otherwise specified)



Remark The graphs indicate nominal characteristics.

REFERENCE

Document Name	Document No.
Opto-Electronics Devices Pamphlet	PX10160E

SAFETY INFORMATION ON THIS PRODUCT

Caution	GaAs Products	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none"> • Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below. 1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials. 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal. • Do not burn, destroy, cut, crush, or chemically dissolve the product. • Do not lick the product or in any way allow it to enter the mouth.
Caution	Optical Fiber	<p>A glass-fiber is attached on the product. Handle with care.</p> <ul style="list-style-type: none"> • When the fiber is broken or damaged, handle carefully to avoid injury from the damaged part or fragments.